

FIG. 1A

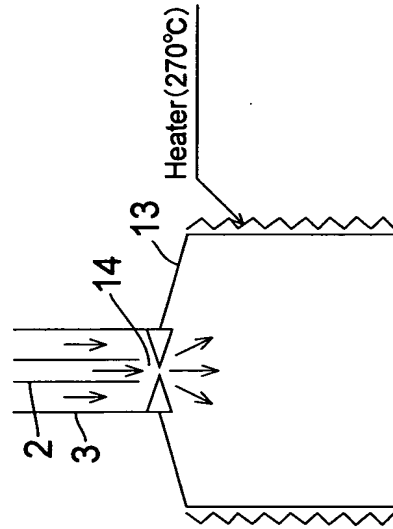


FIG. 1B

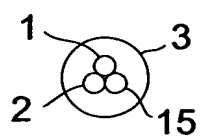


FIG. 2C

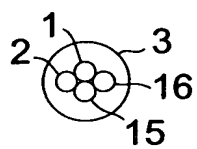


FIG. 2D

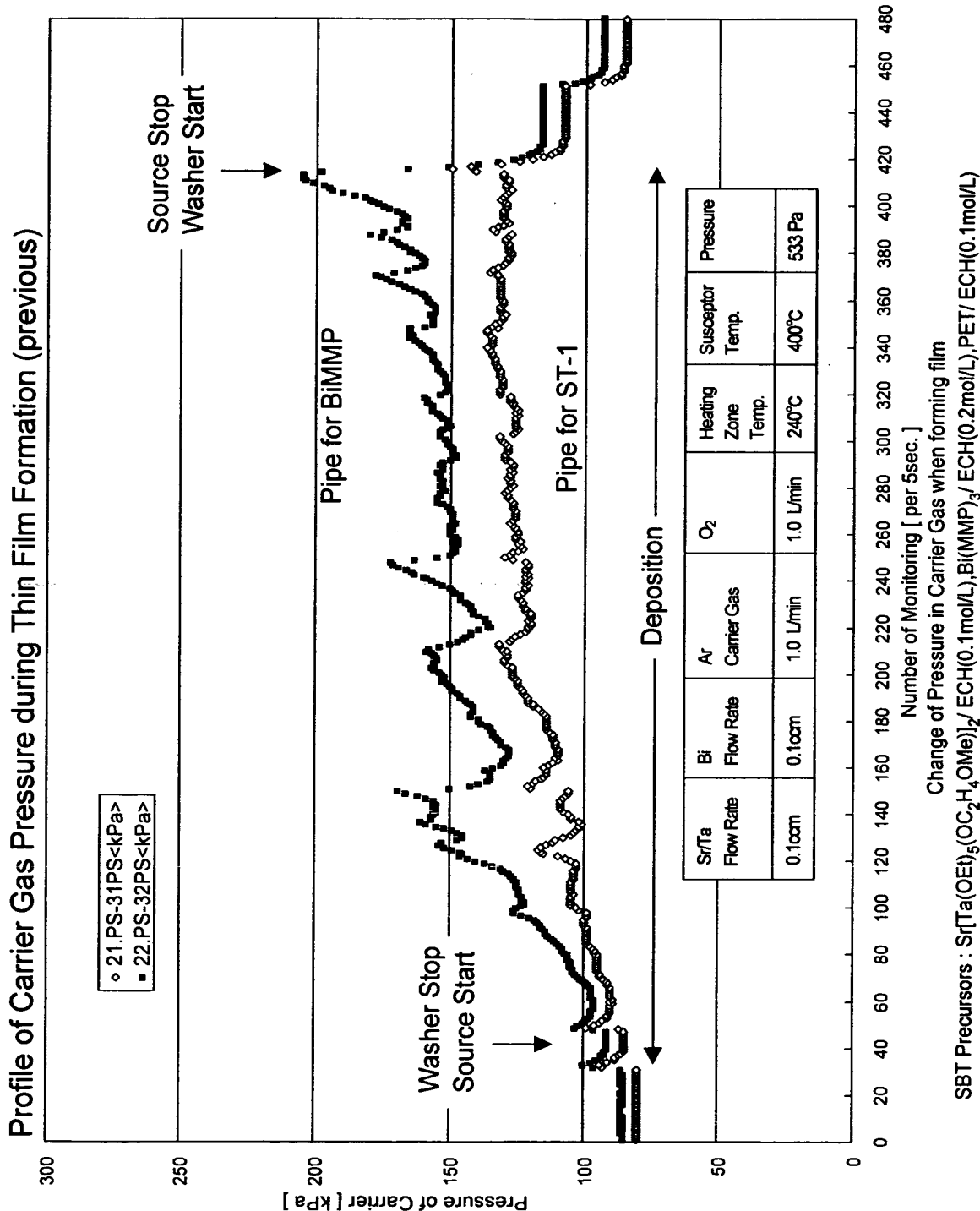


FIG.3

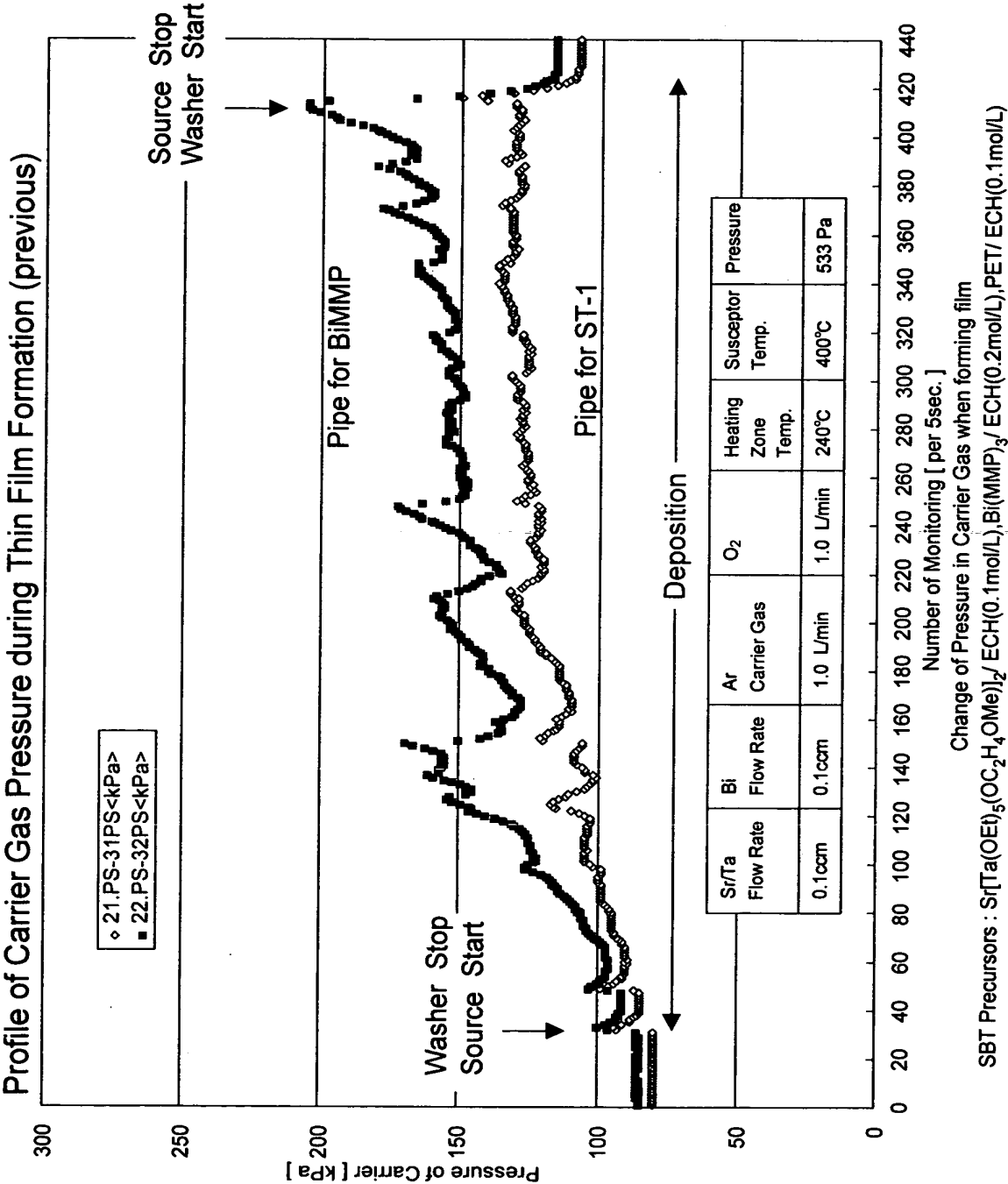


FIG.4

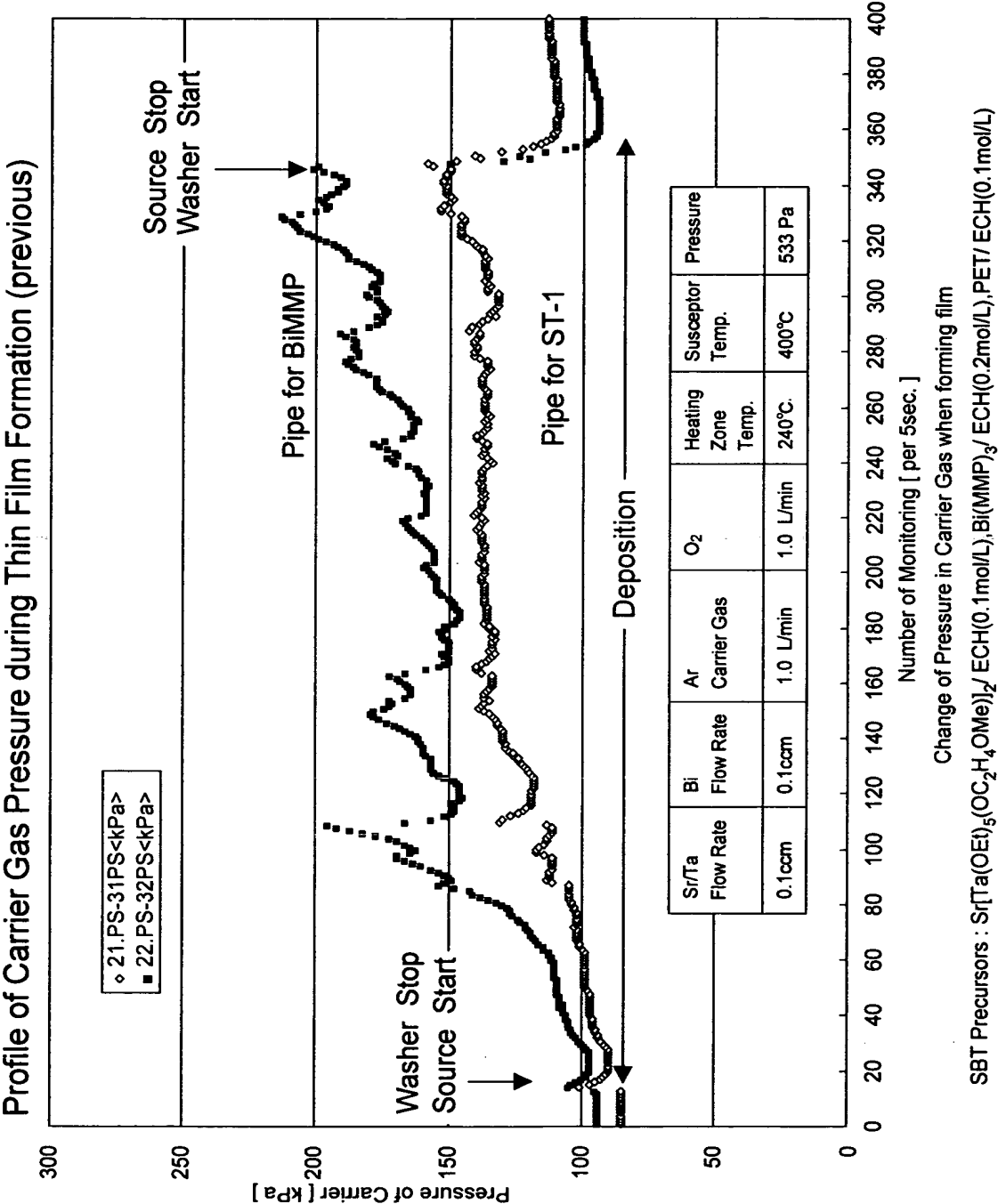
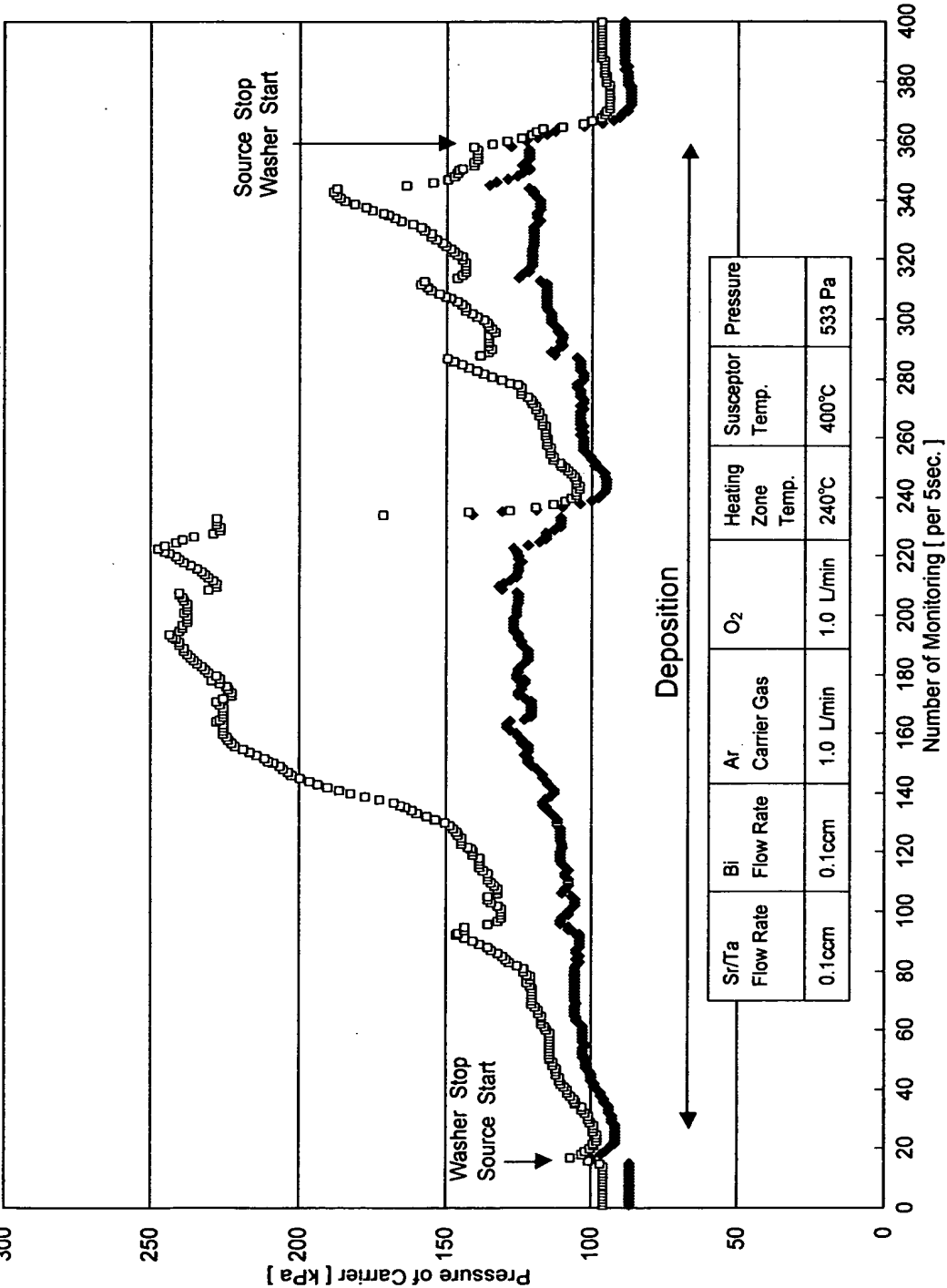


FIG.5

Profile of Carrier Gas Pressure during Thin Film Formation (previous)



Change of Pressure in Carrier Gas when forming film
SBT Precursors : Sr[Ta(OEt)₅(OC₂H₄OMe)]₂/ ECH(0.1mol/L),Bi(MMP)₃/ ECH(0.2mol/L),PET/ ECH(0.1mol/L)

FIG.6

Profile of Carrier Gas Pressure during Thin Film Formation (previous)

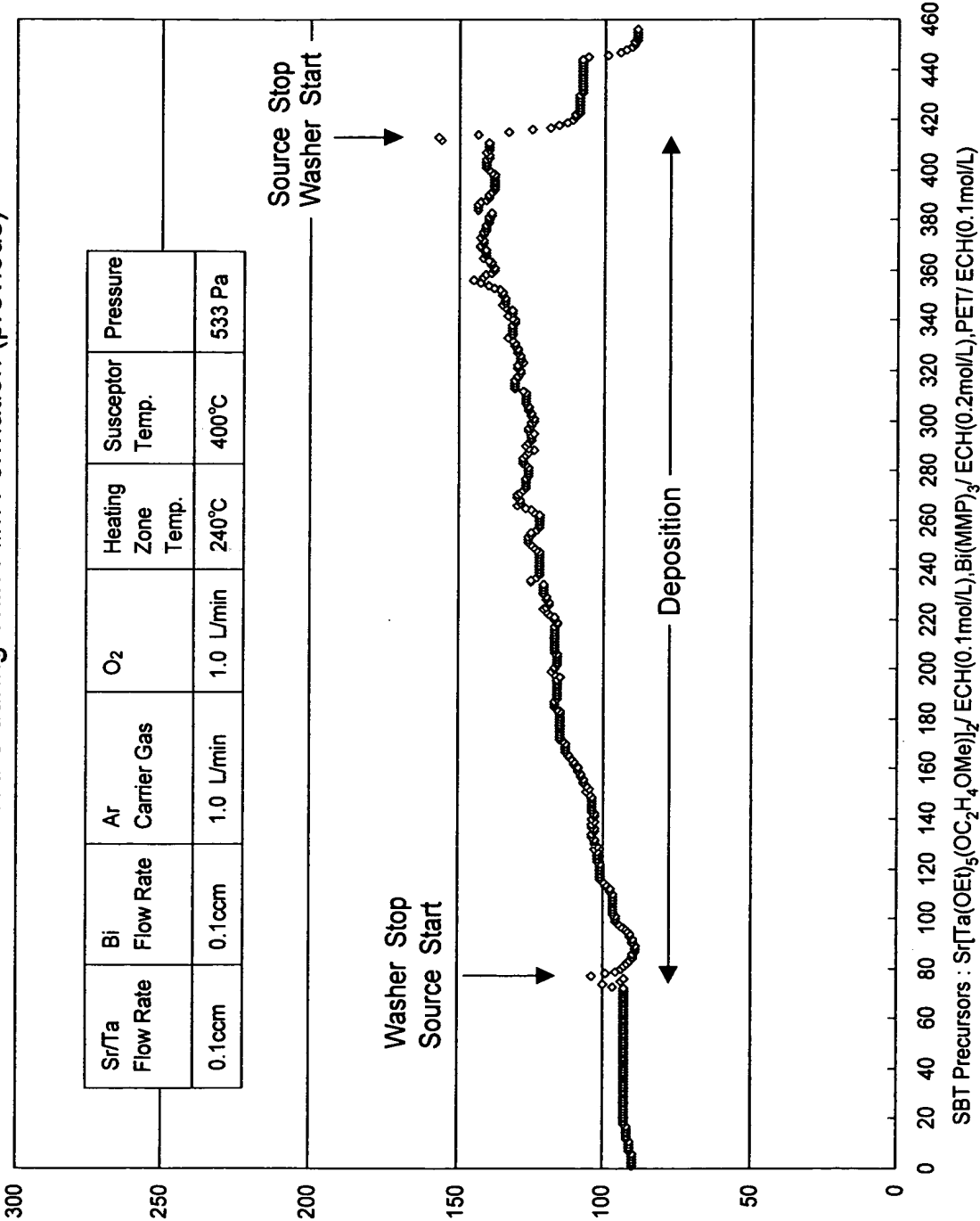
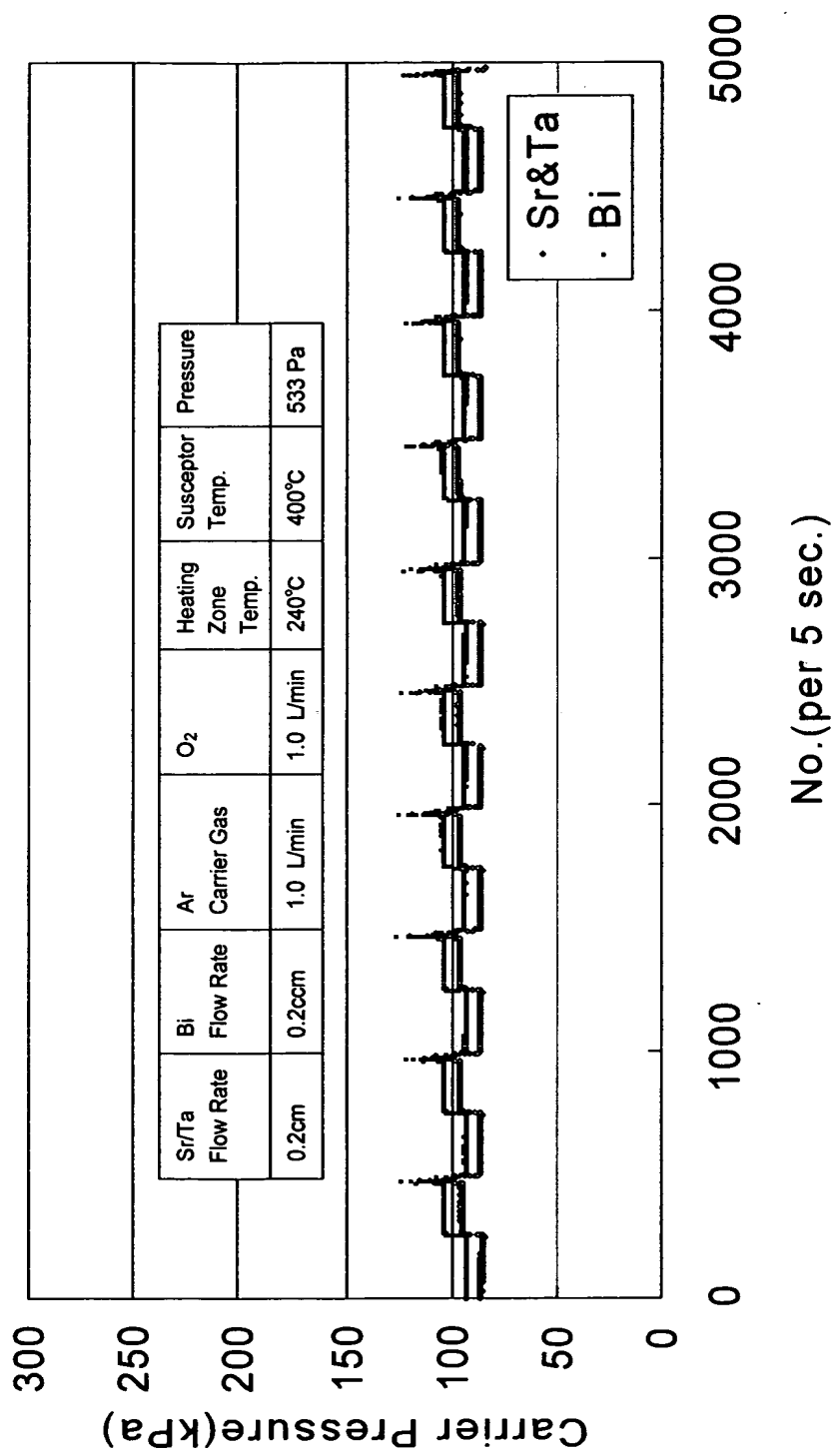


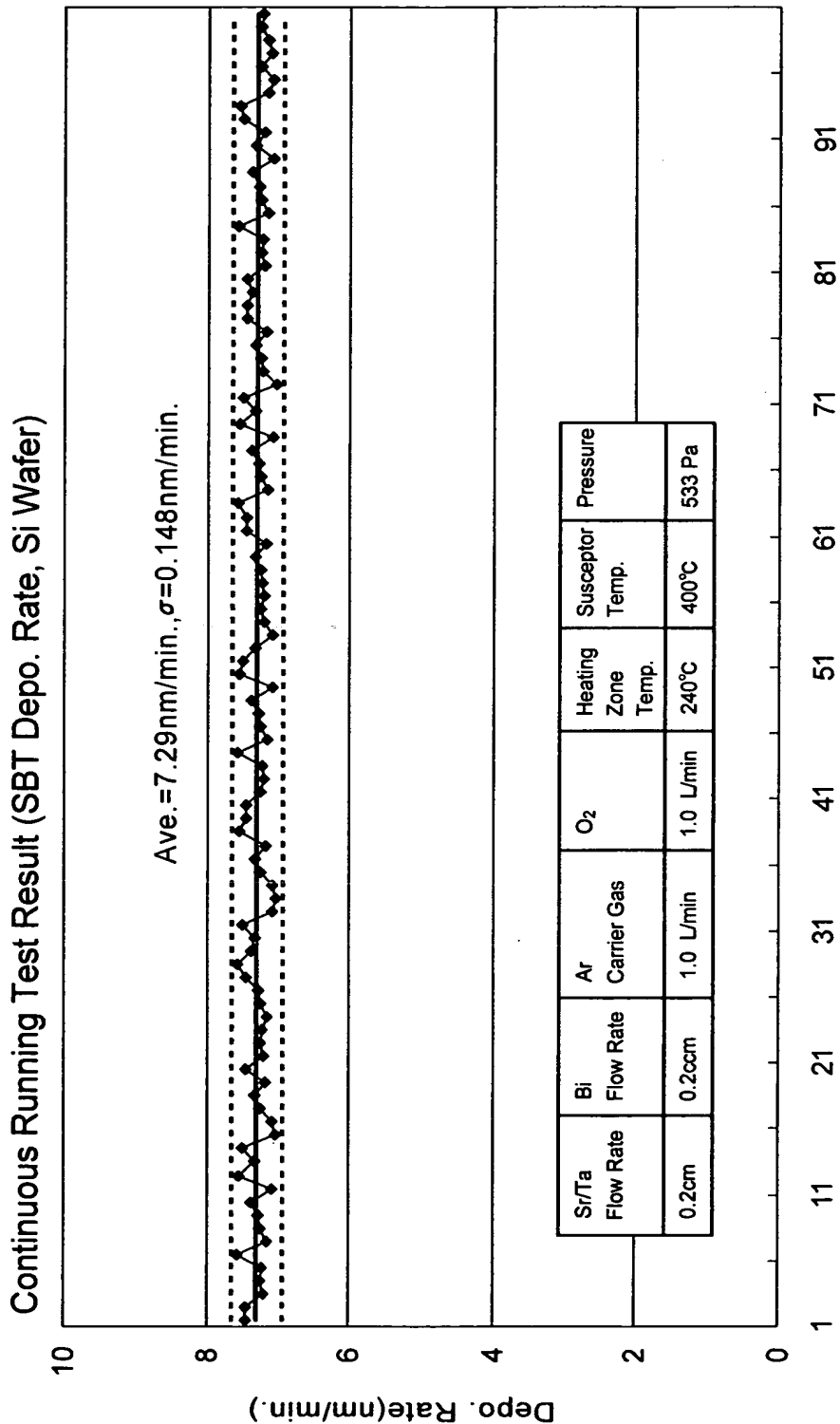
FIG.7

Profile of Carrier Gas Pressure during Thin Film Formation (Current)



SBT Precursors : Sr[Ta(OEt)₅(OC₂H₄OMe)]₂/ ECH(0.05mol/L), Bi(MMP)₃/ ECH(0.1mol/L), PET/ ECH(0.05mol/L)

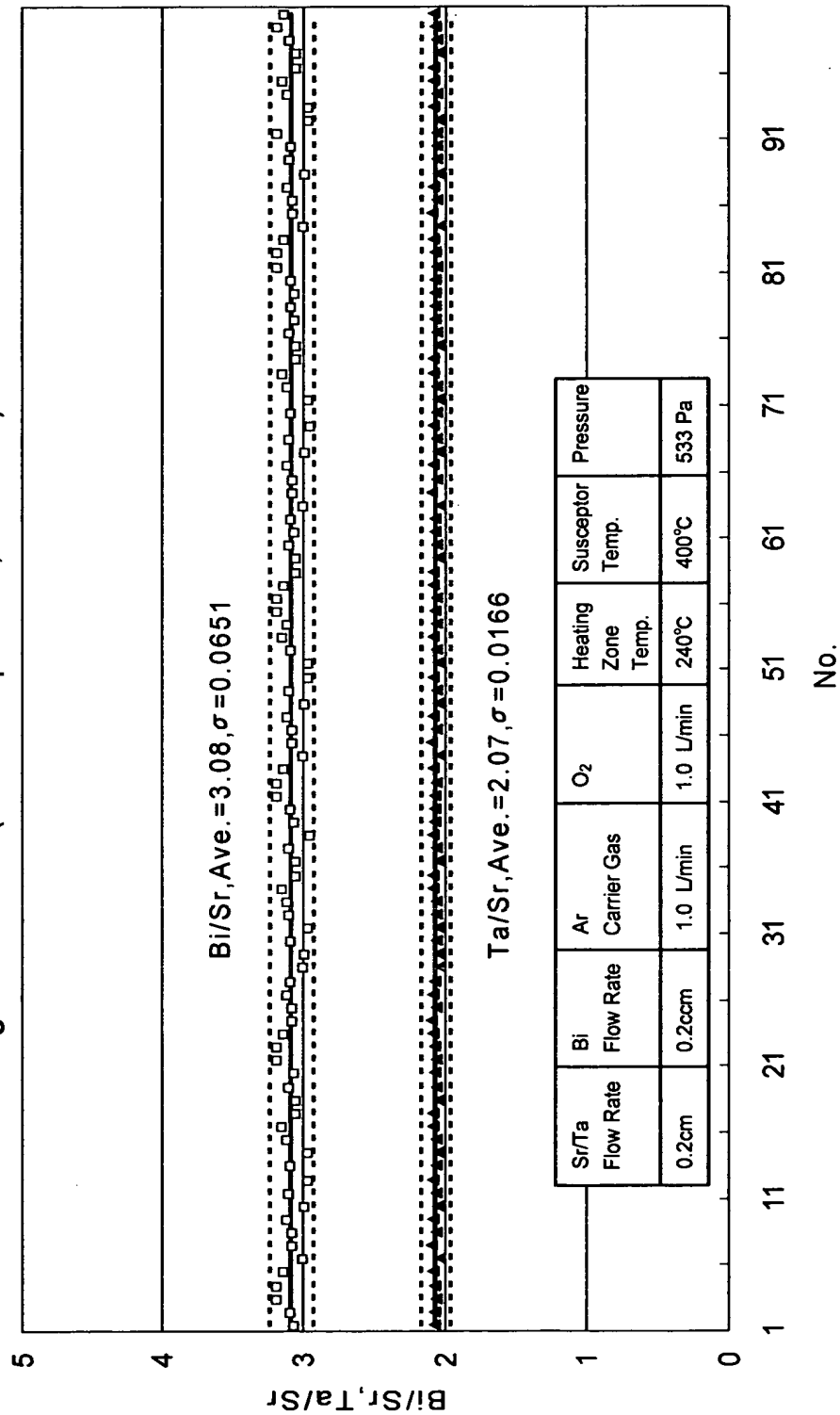
FIG.8



SBT Precursors : $\text{Sr}[\text{Ta}(\text{OEt})_3(\text{OC}_2\text{H}_4\text{OMe})]_2 / \text{ECH}(0.05\text{mol/L}), \text{Bi}(\text{MMP})_3 / \text{ECH}(0.1\text{mol/L}), \text{PET} / \text{ECH}(0.05\text{mol/L})$

FIG.9

Continuous Running Test Result (SBT Composition, Si Wafer)



SBT Precursors : $\text{Sr}[\text{Ta}(\text{OEt})_5(\text{OC}_2\text{H}_4\text{OMe})]_2 / \text{ECH}(0.05\text{mol/L}), \text{Bi}(\text{MMP})_3 / \text{ECH}(0.1\text{mol/L}), \text{PET} / \text{ECH}(0.05\text{mol/L})$

FIG.10

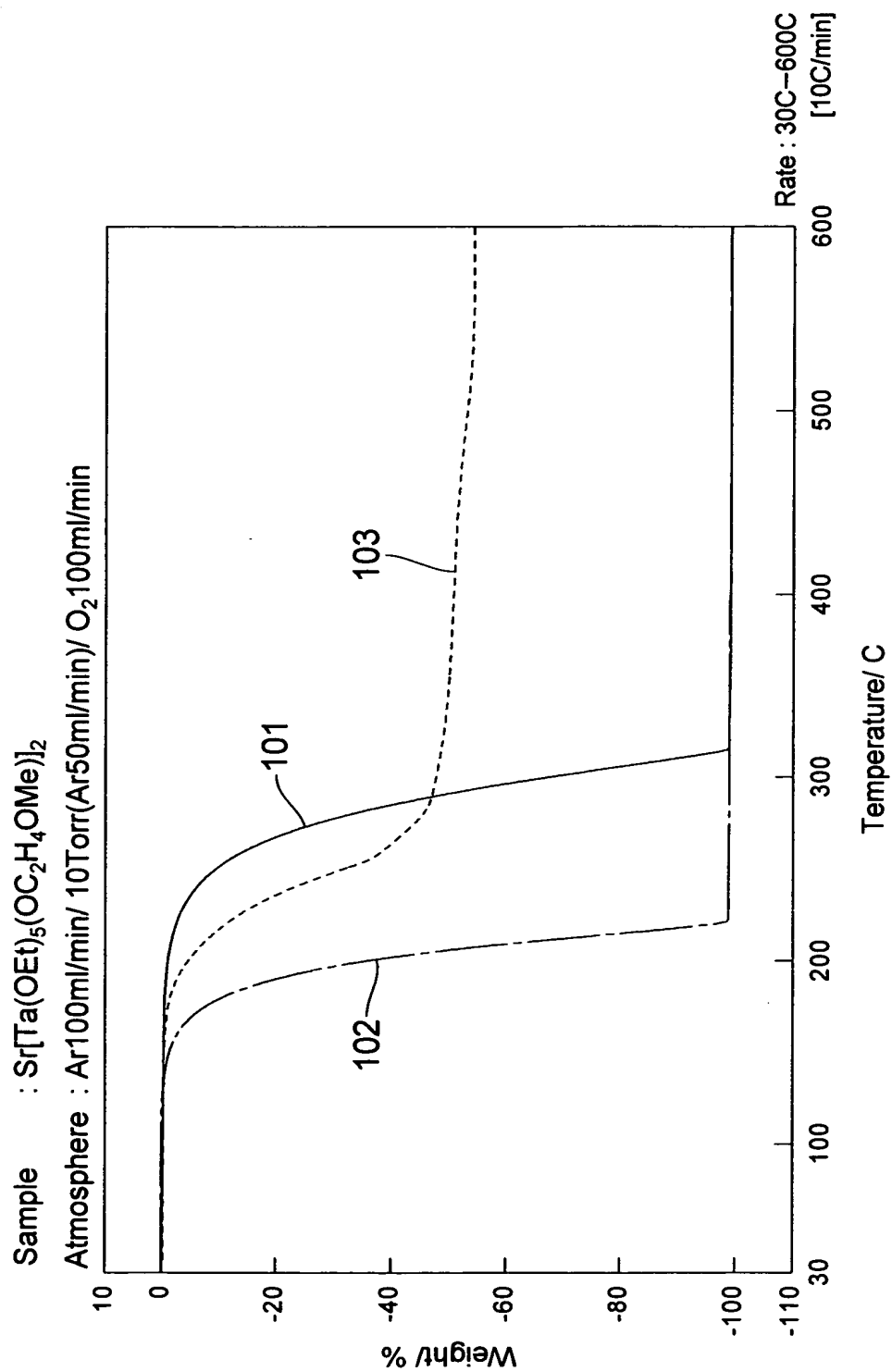


FIG. 11

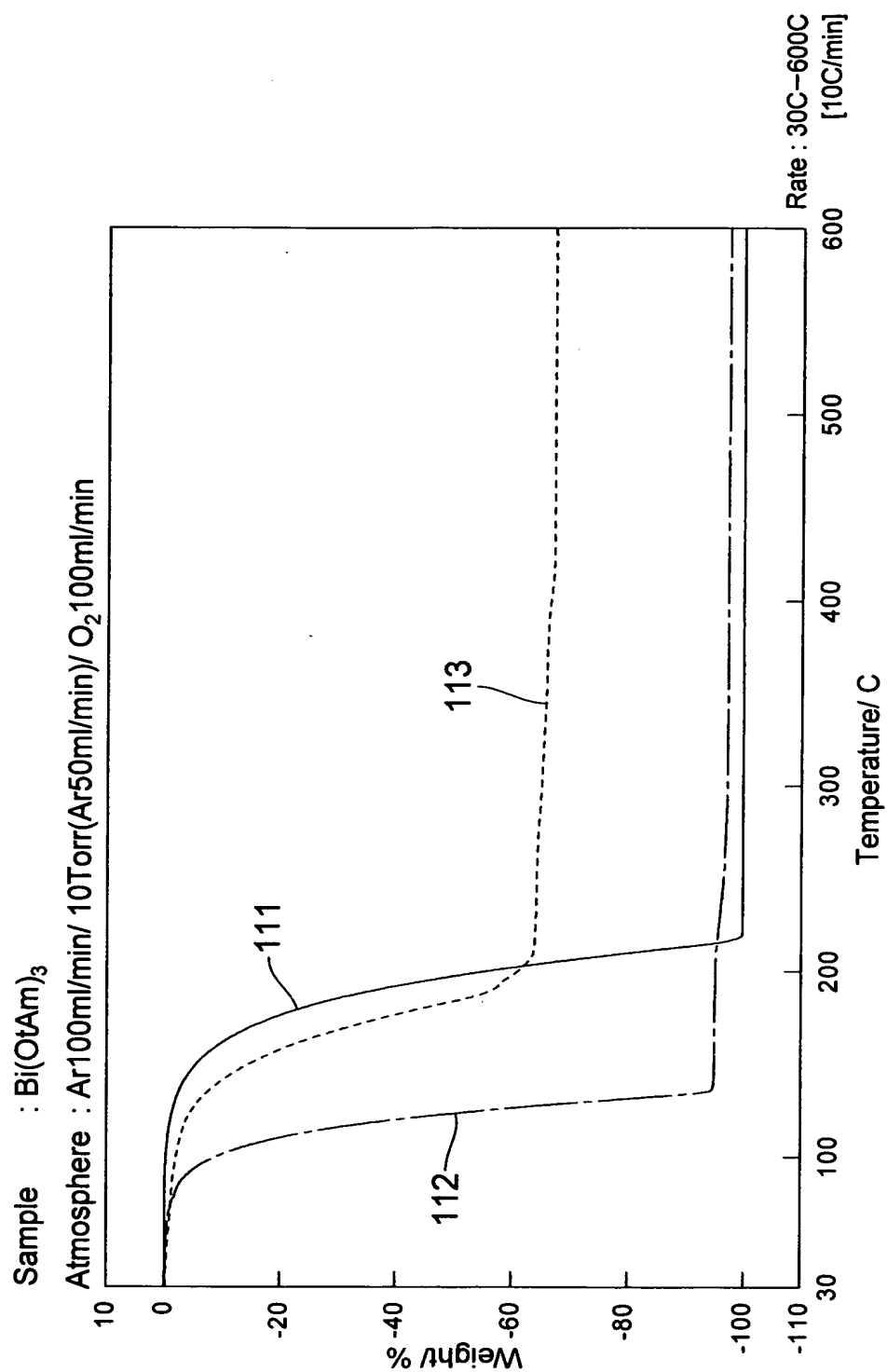


FIG.12

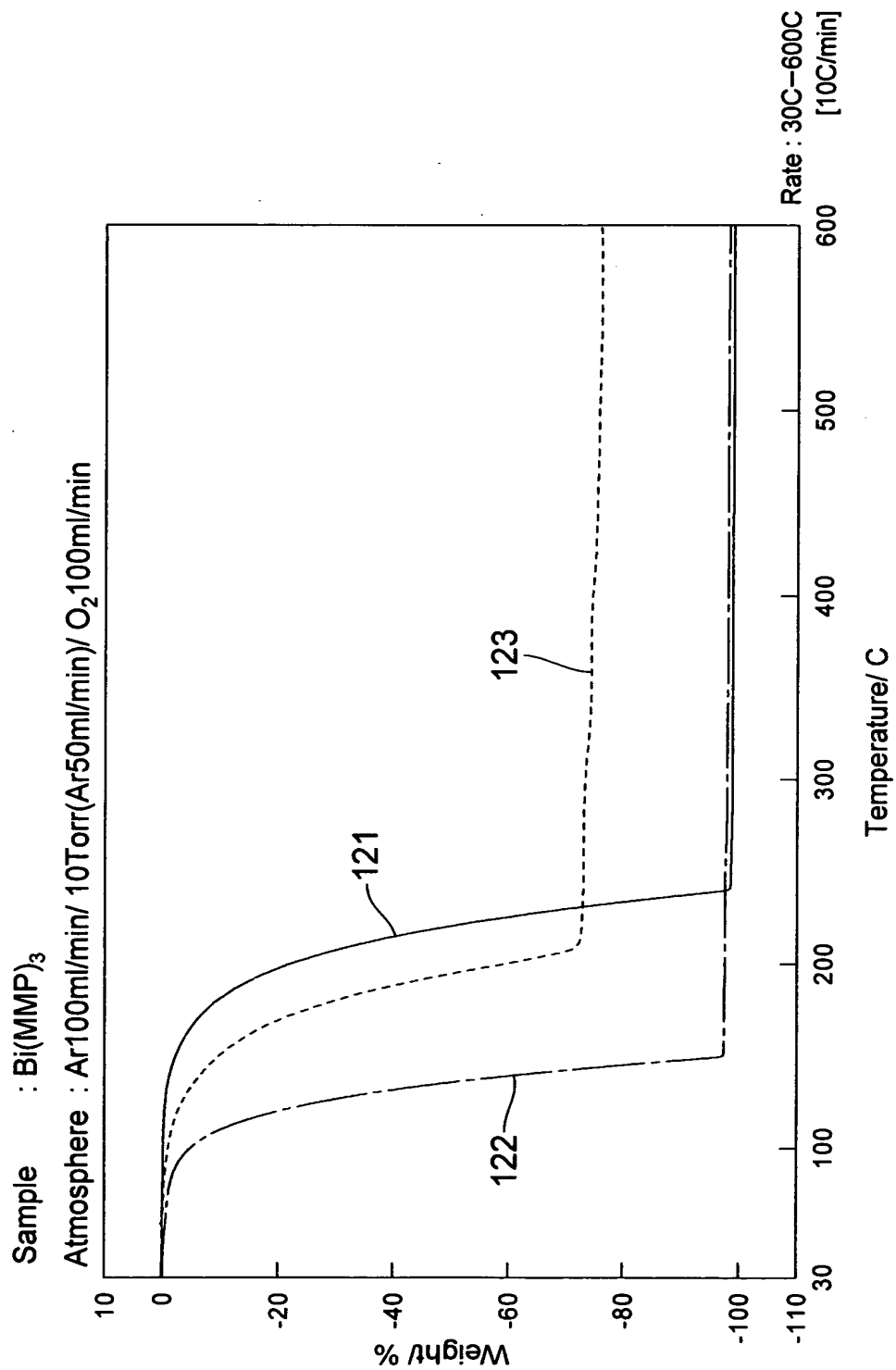


FIG.13

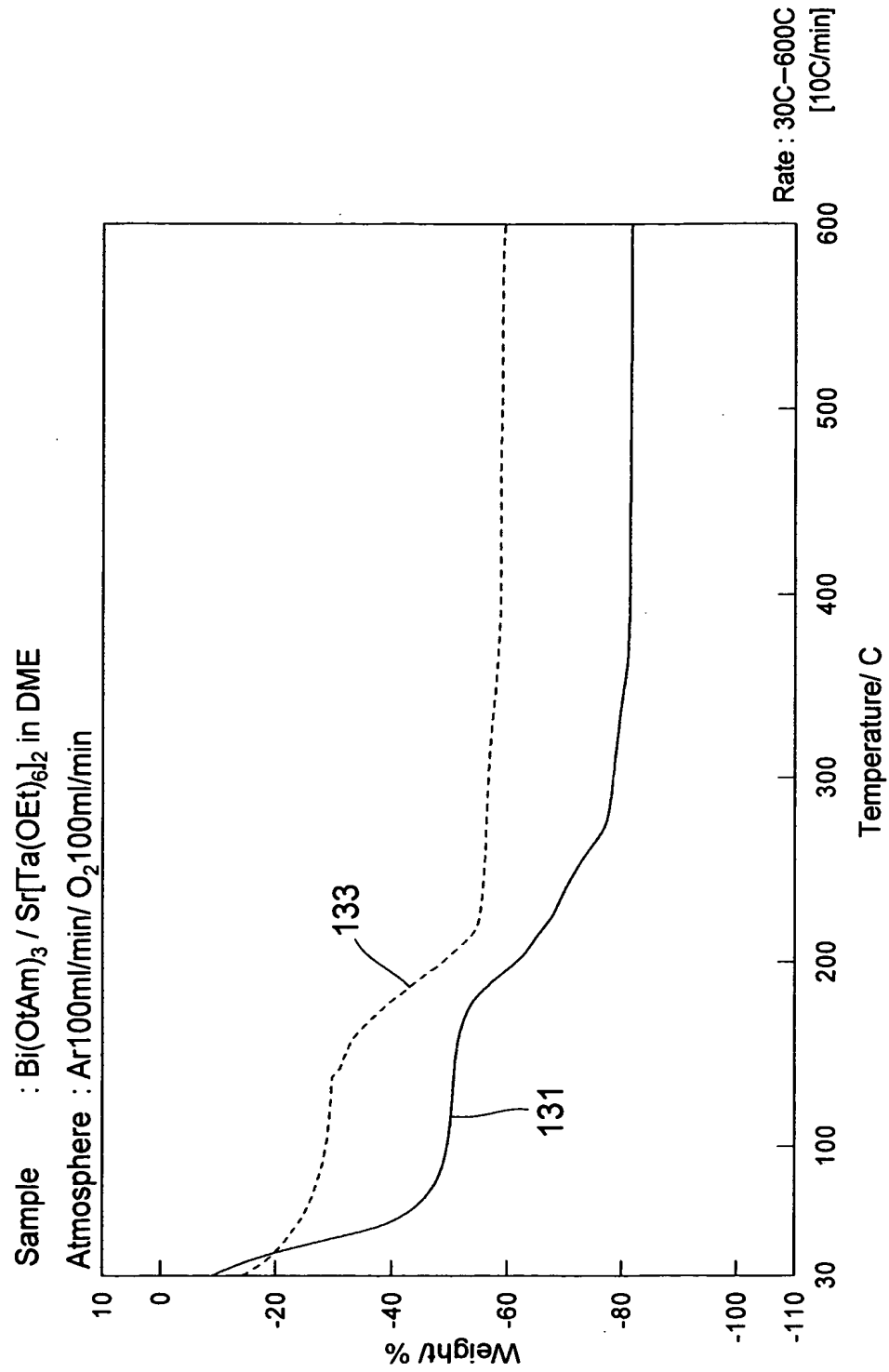


FIG.14

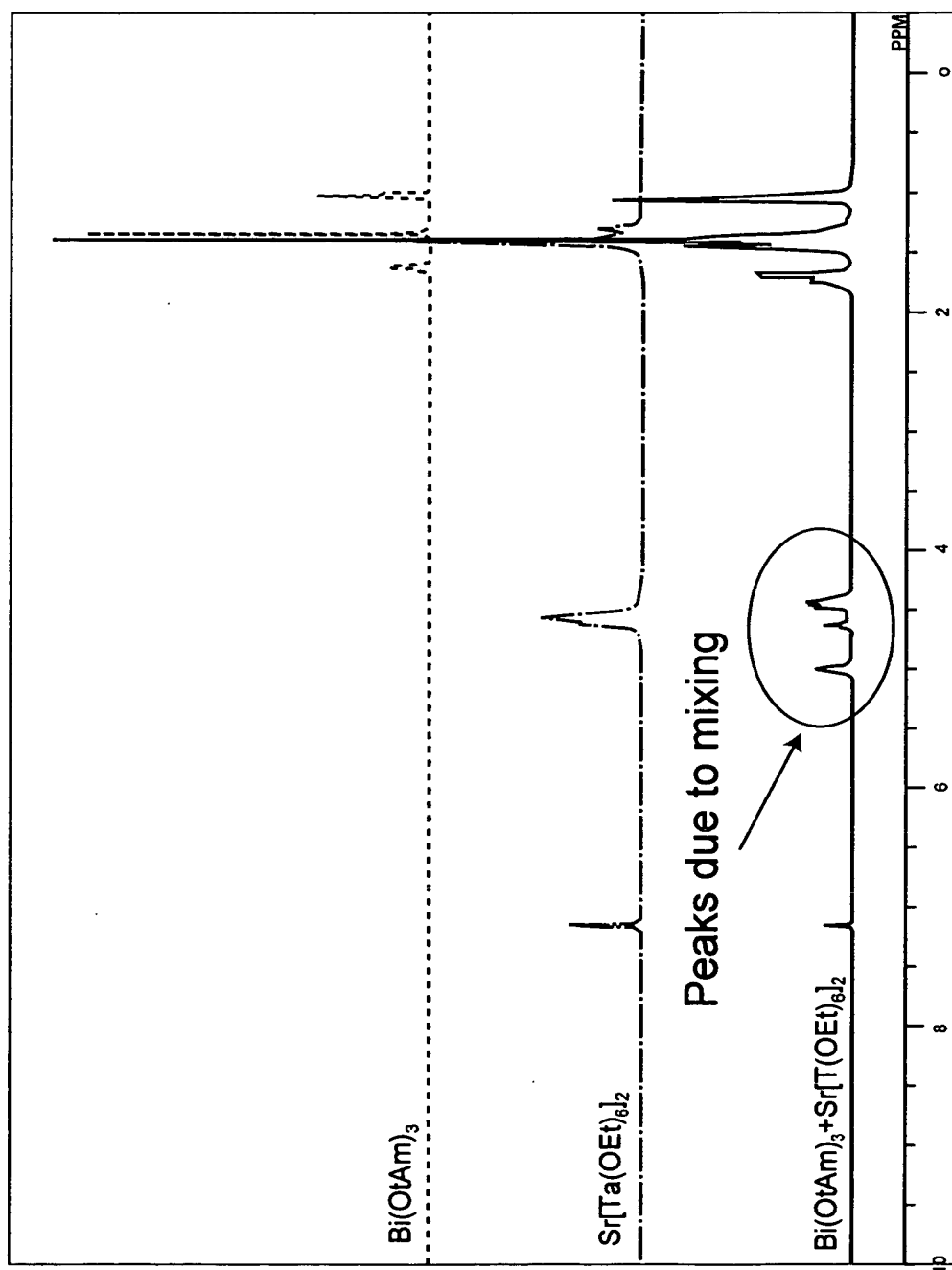


FIG.15

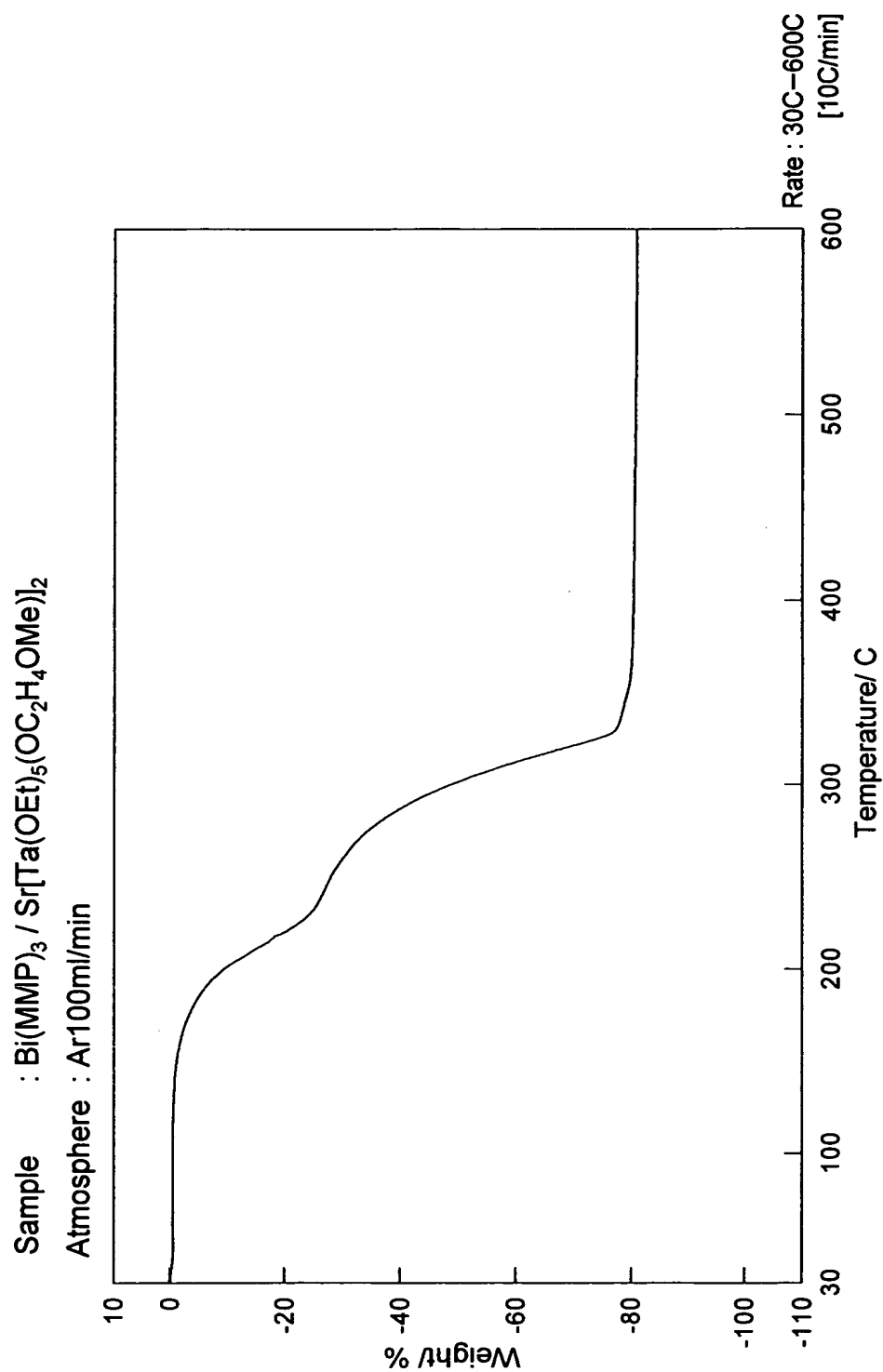


FIG.16

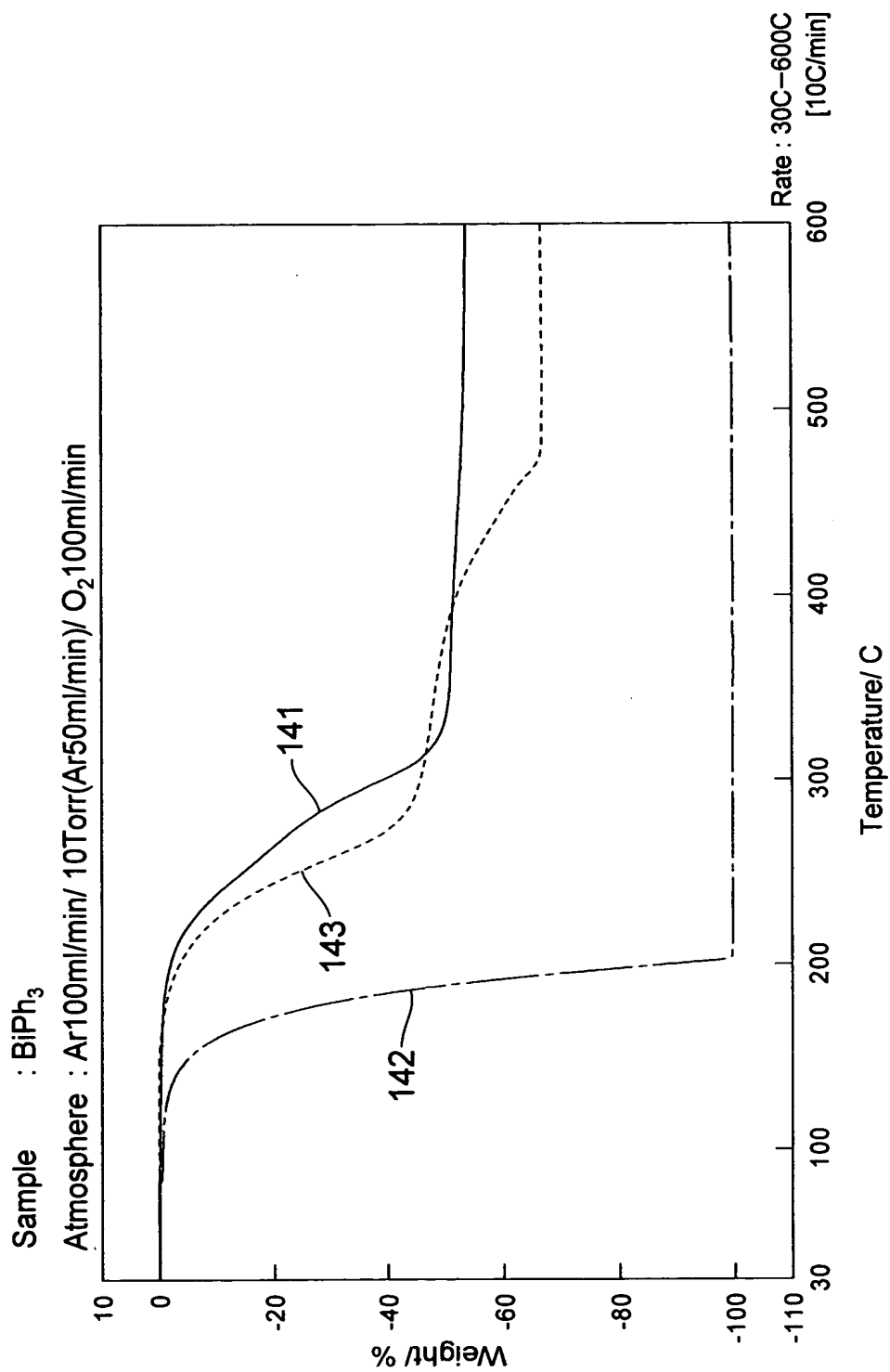


FIG.17

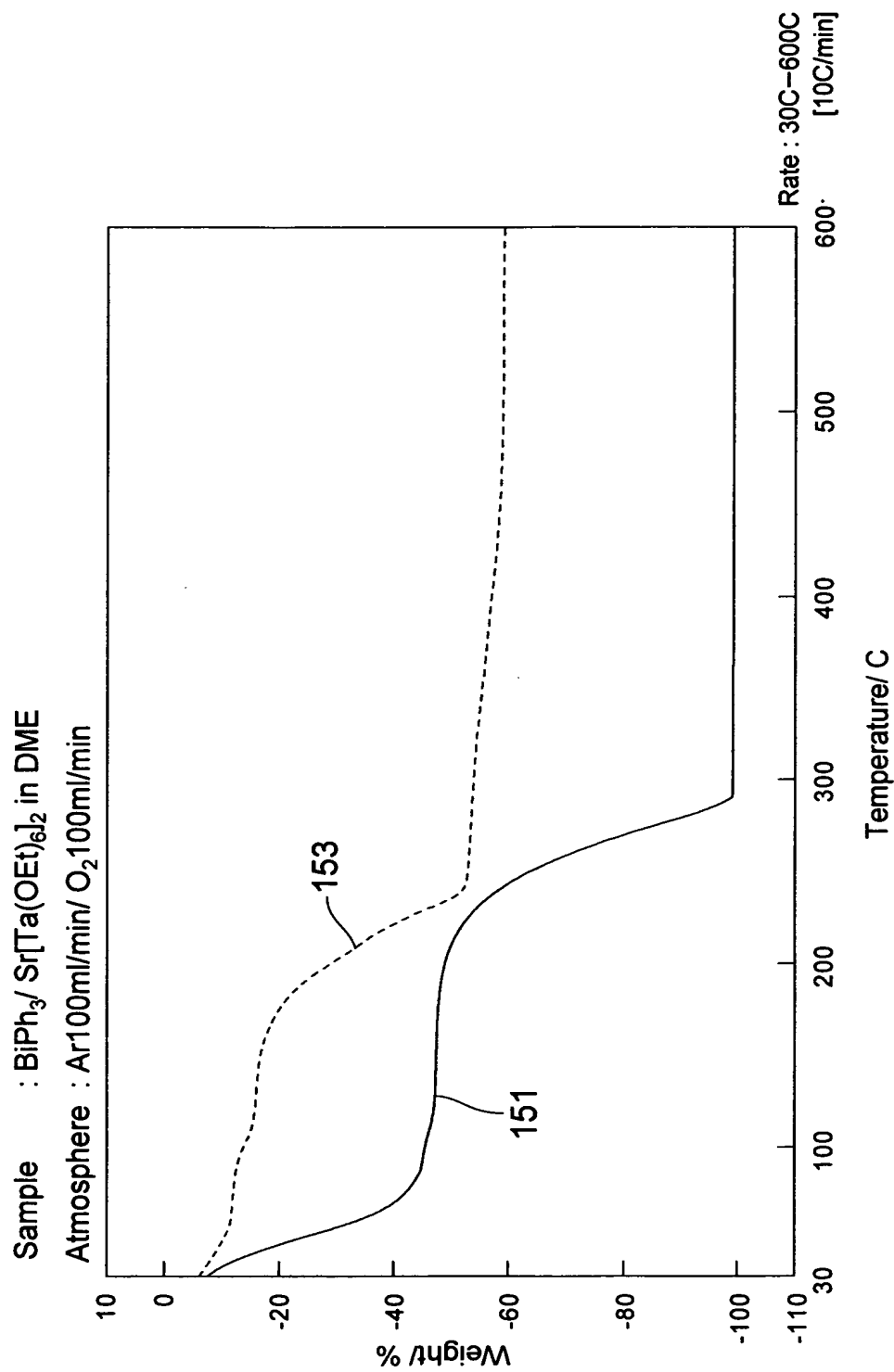


FIG.18

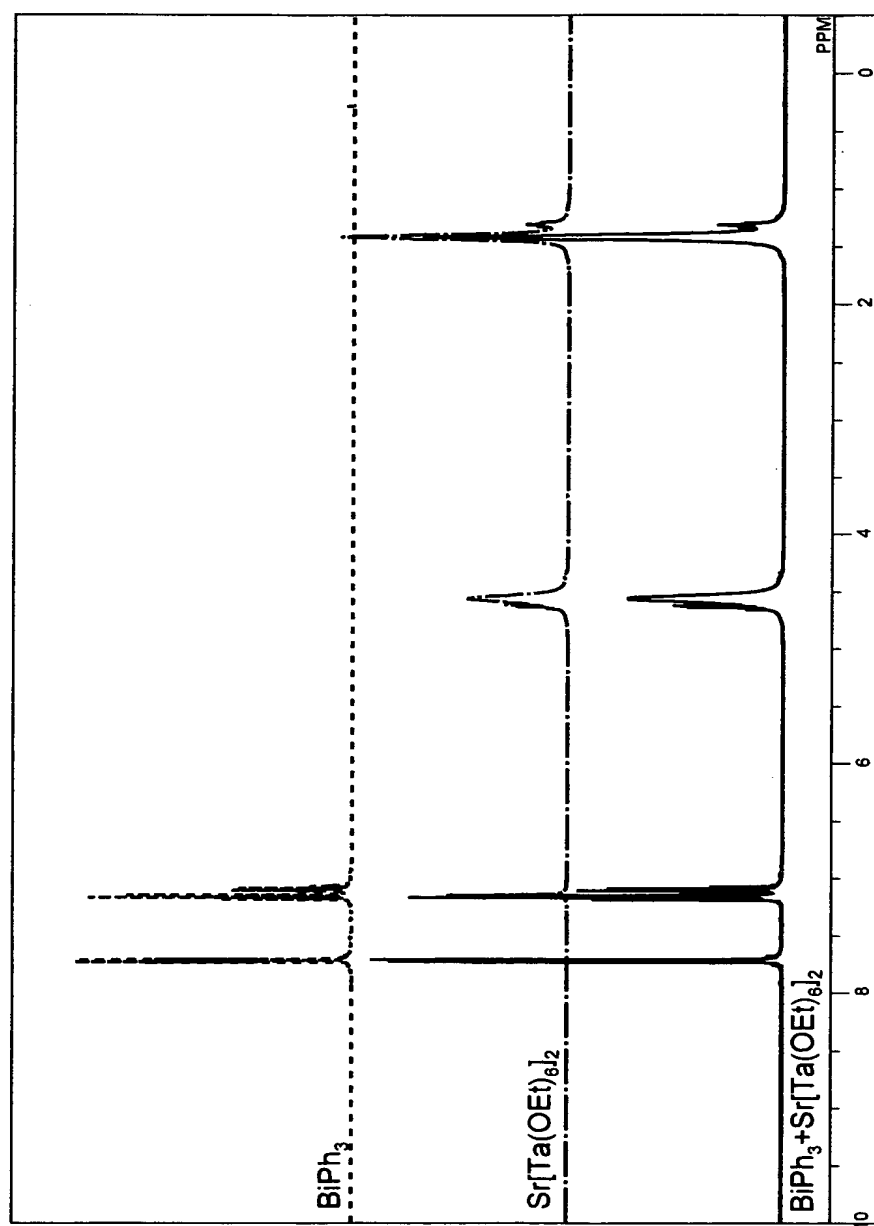


FIG.19

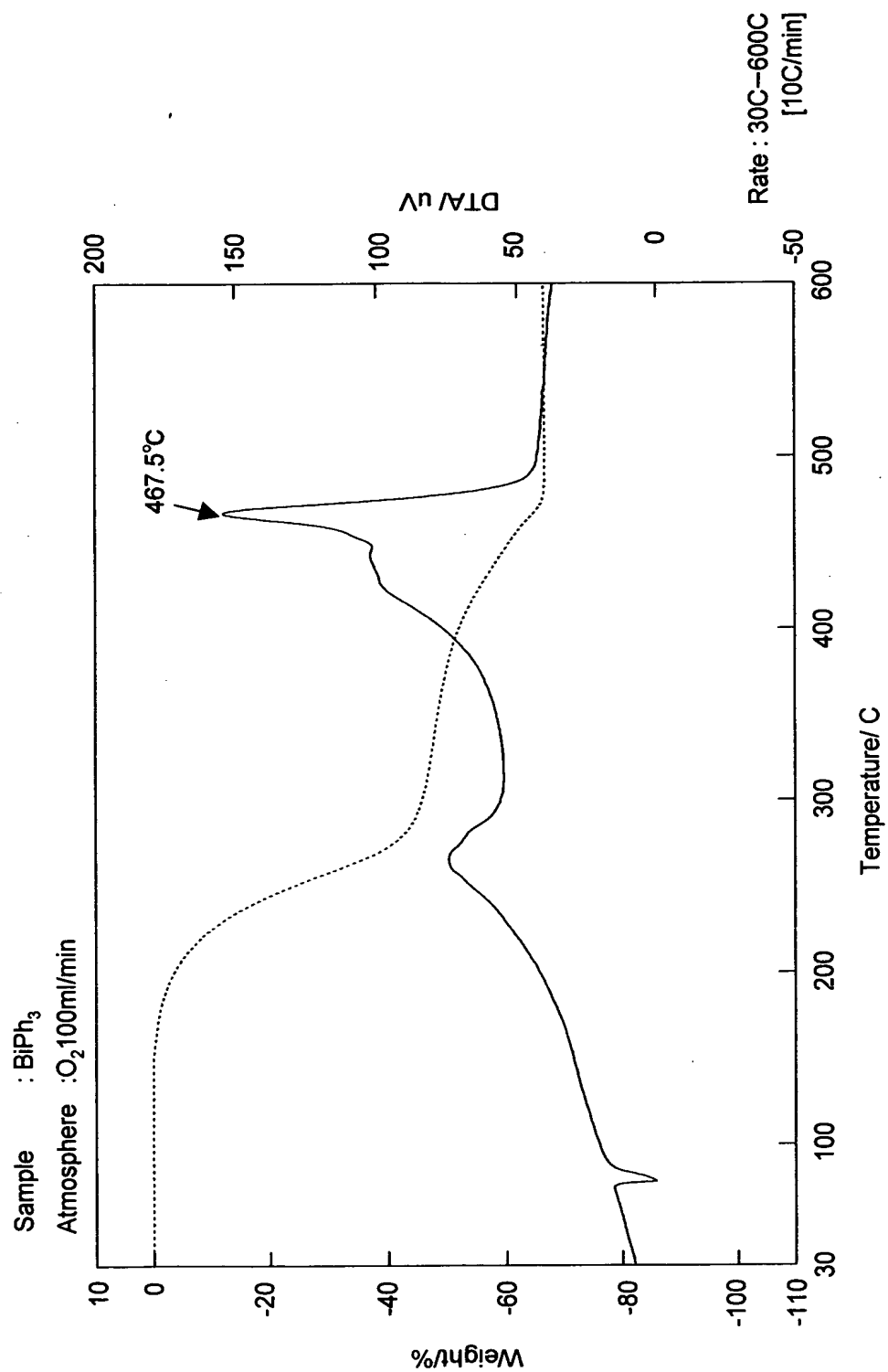


FIG.20